

Description

The LM3400A uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

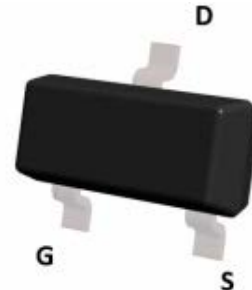
General Features

- $V_{DS} = 30V$ $I_D = 5.8A$
- $R_{DS(ON)} < 28m\Omega$ @ $V_{GS}=10V$

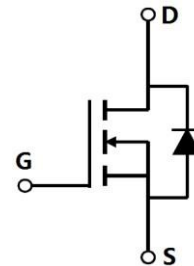
Application

- Lithium battery protection
- Wireless impact
- Mobile phone fast charging

Dimensions SOT-23



Pin Configuration



Package Marking and Ordering Information

Device	Device Marking	Device Package	Reel Size	Tape width	Quantity
LM3400A	A09T	SOT-23	-	-	3000 units

Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current	5.8	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current	4.9	A
I_{DM}	Pulsed Drain Current ²	20	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation ³	1	W
TSTG	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	125	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ (t ≤ 10s)	85	°C/W

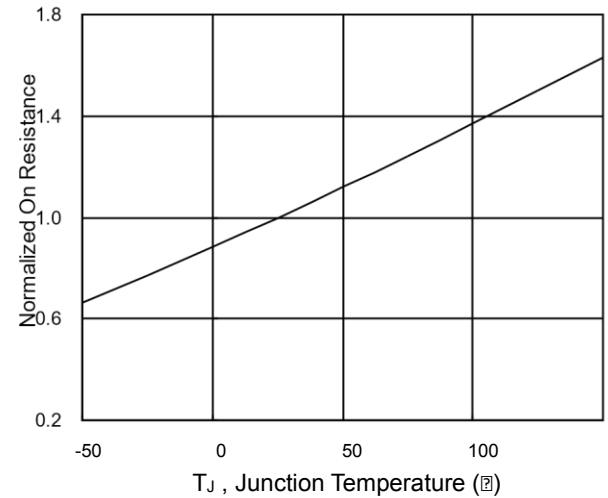
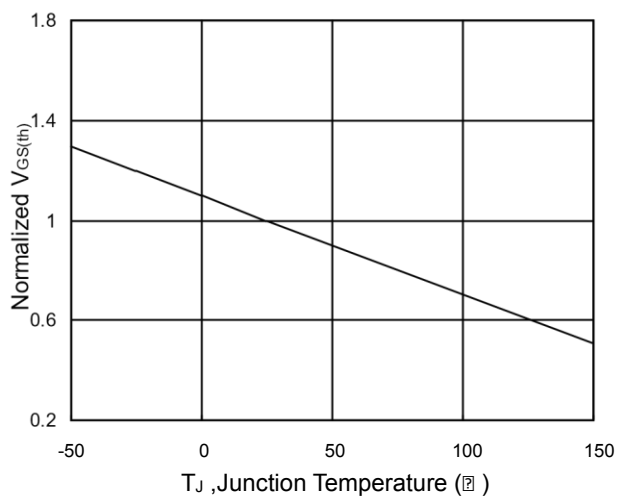
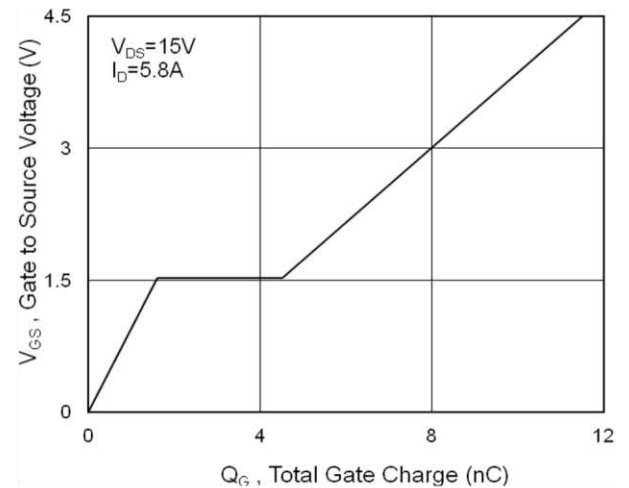
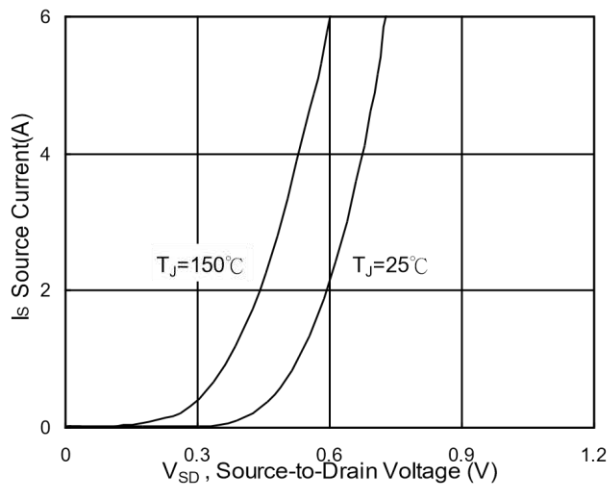
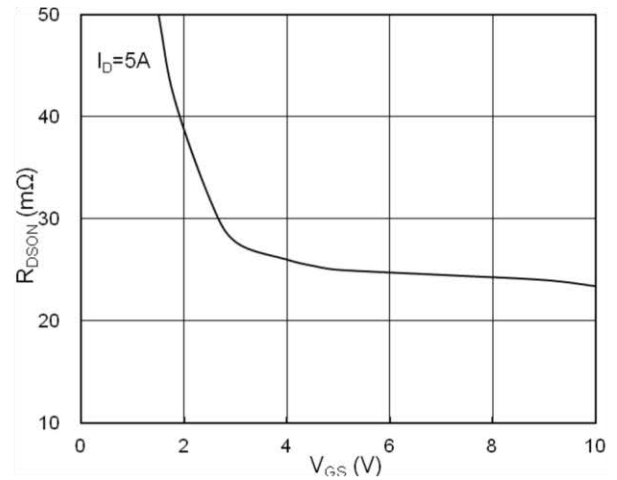
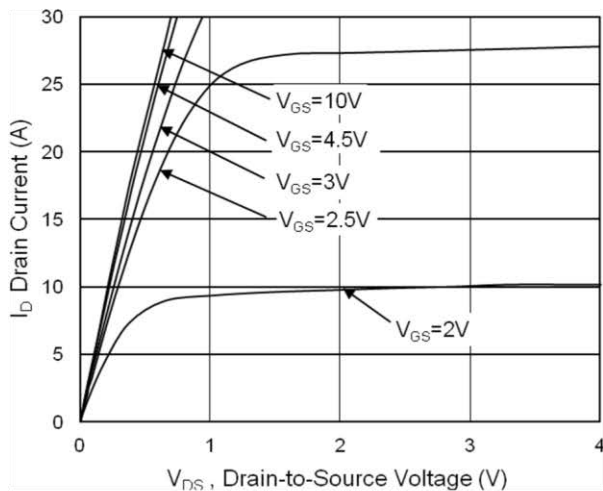
Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	33	---	V
ΔBVDSS/ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.029	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =5.8A	---	20	28	mΩ
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =5A	---	24	32	mΩ
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =2.5V, I _D =4A	---	31	55	mΩ
VGS(th)	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	0.5	0.85	1.2	V
ΔVGS(th)	VGS(th) Temperature Coefficient		---	-2.82	---	mV/°C
IDSS	Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =55°C	---	---	5	
IGSS	Gate-Source Leakage Current	V _{GS} =±12V, V _{DS} =0V	---	---	±100	nA
gfs	Forward Transconductance	V _{DS} =5V, I _D =5A	---	25	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.5	---	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =15V, V _{GS} =4.5V, I _D =5.8A	---	11.5	---	nC
Q _{gs}	Gate-Source Charge		---	1.6	---	
Q _{gd}	Gate-Drain Charge		---	2.9	---	
Td(on)	Turn-On Delay Time	V _{DD} =15V, V _{GS} =10V, R _G =3Ω I _D =5A	---	5	---	ns
T _r	Rise Time		---	47.	---	
Td(off)	Turn-Off Delay Time		---	26	---	
T _f	Fall Time		---	8	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	860	---	pF
C _{oss}	Output Capacitance		---	84	---	
C _{rss}	Reverse Transfer Capacitance		---	70	---	
I _s	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	5.8	A
VSD	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3、The power dissipation is limited by 150°C junction temperature
- 4、The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Electrical and Thermal Characteristics



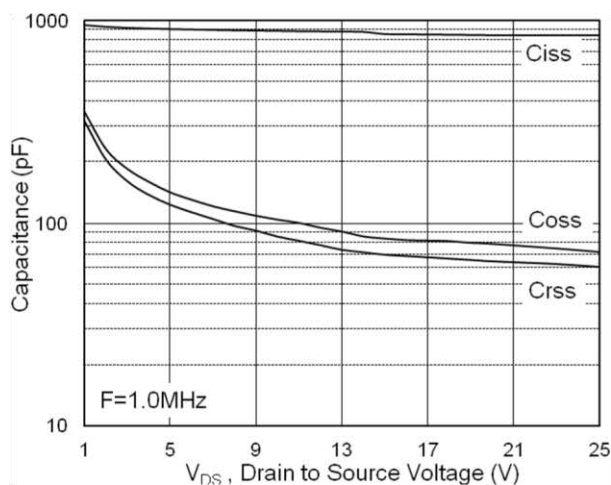


Fig.7 Capacitance

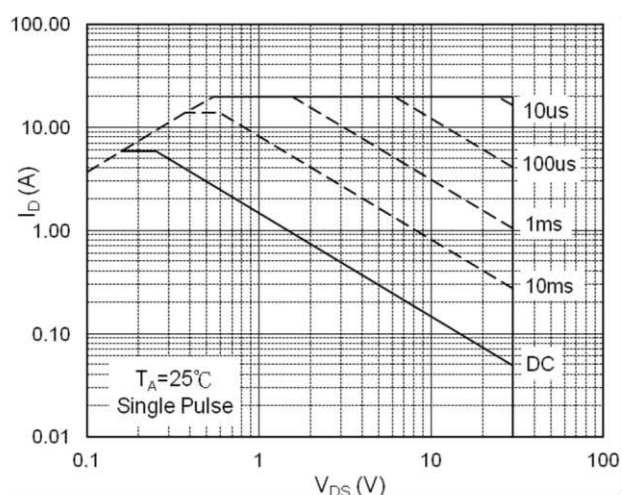


Fig.8 Safe Operating Area

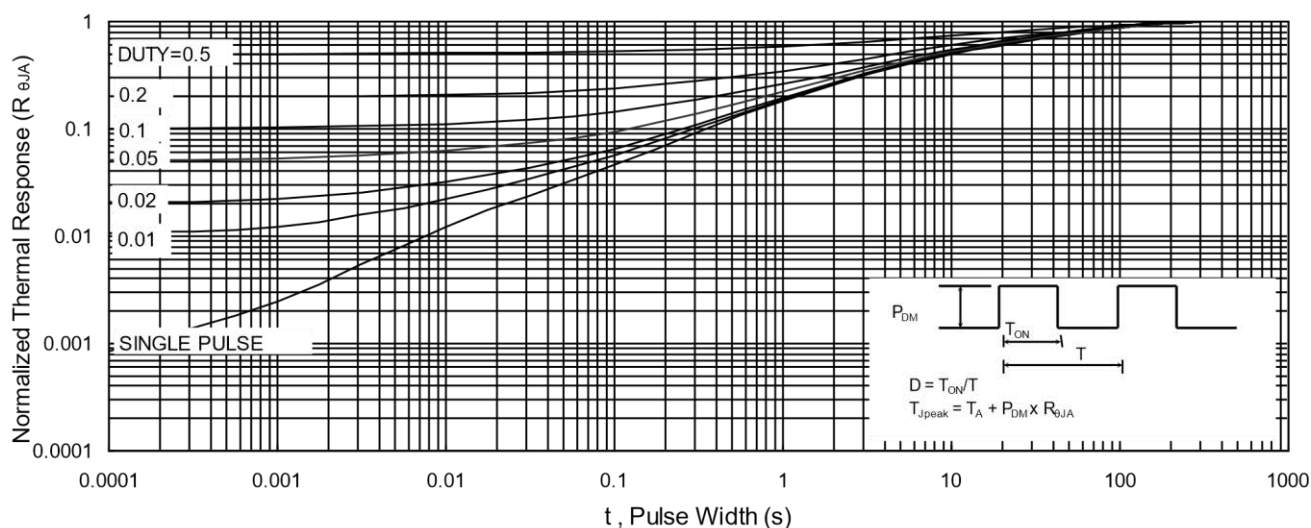


Fig.9 Normalized Maximum Transient Thermal Impedance

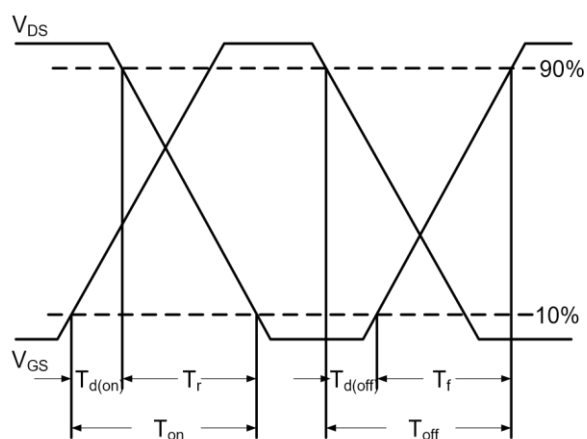


Fig.10 Switching Time Waveform

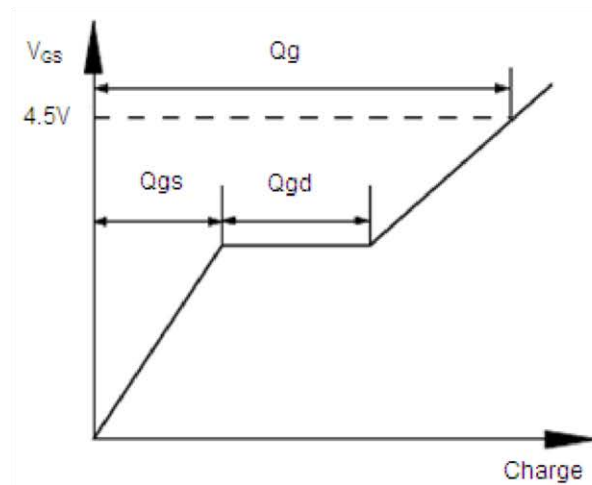
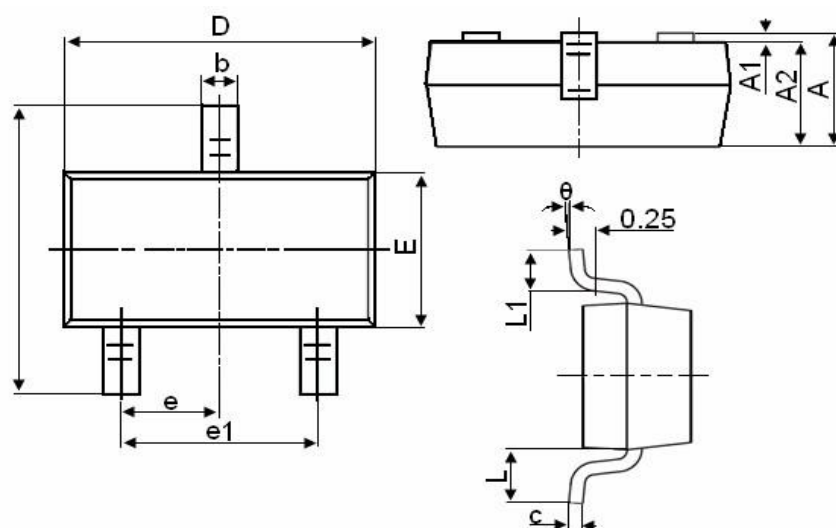


Fig.11 Gate Charge Waveform

Package Mechanical Data-SOT-23



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

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